Page 1 of 48

Matter No.: 14925-011US1 Page 1 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278

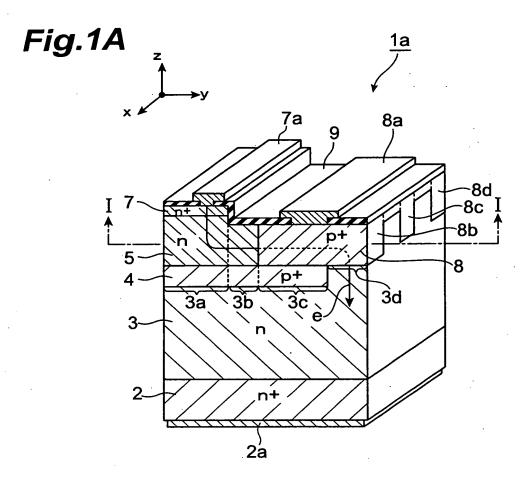
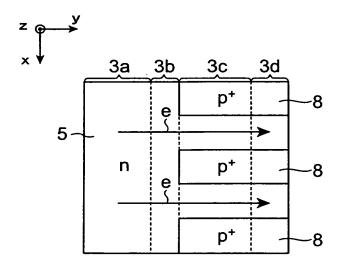


Fig.1B



Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

DEFFECT TRANSISTORS 10/522278

Fig.2A

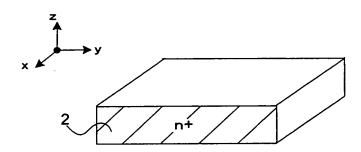


Fig.2B

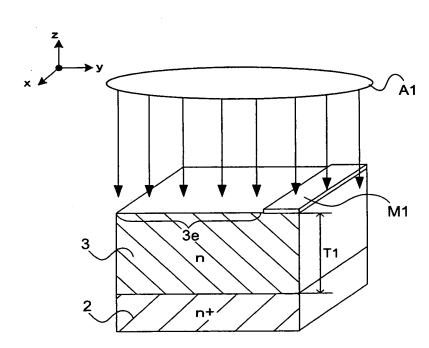
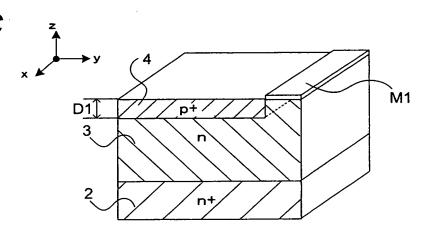


Fig.2C



10/522278

Fig.3A

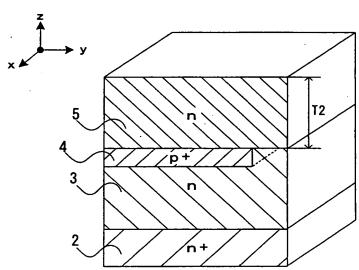
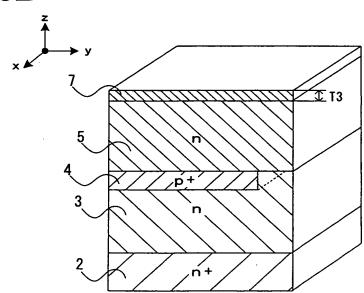
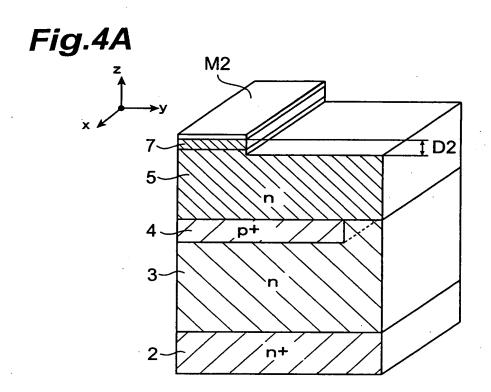
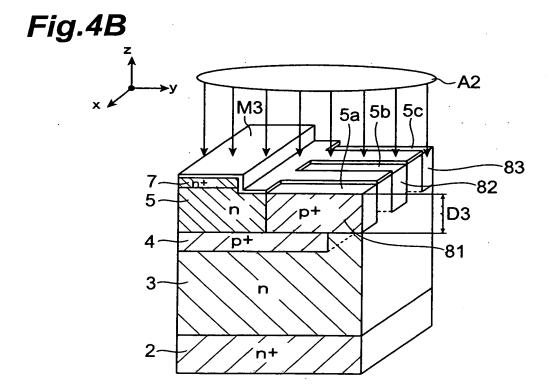


Fig.3B







5/48

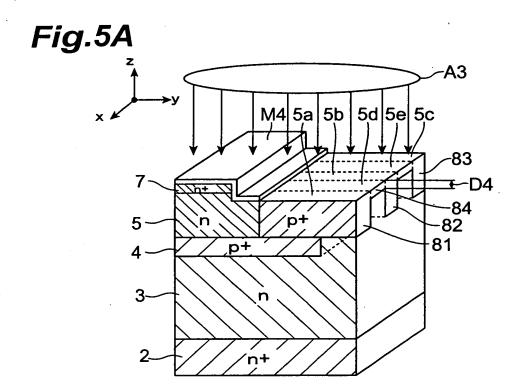
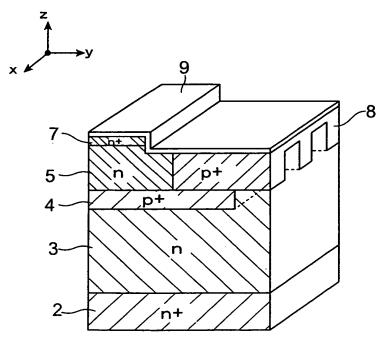


Fig.5B

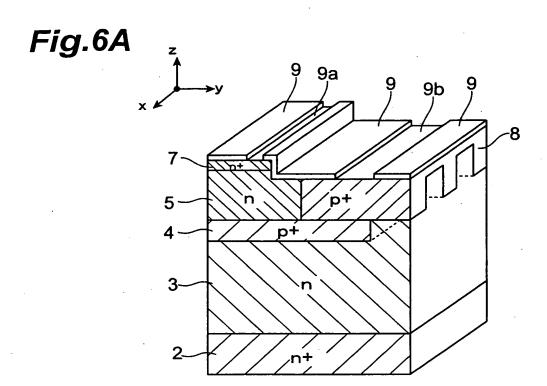


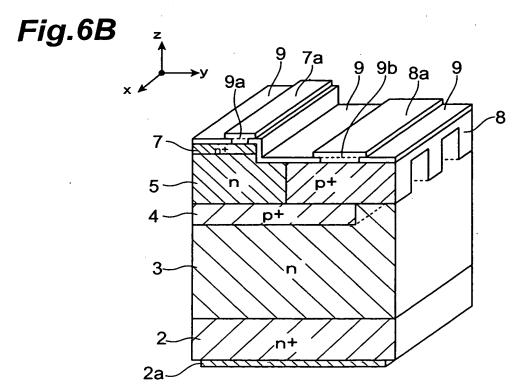
Matter No.: 14925-011US1 Page 6 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHOD OF TRANSISTORS

METHOD OF TRANSISTORS

FIELD EFFECT TRANSISTORS

6/48





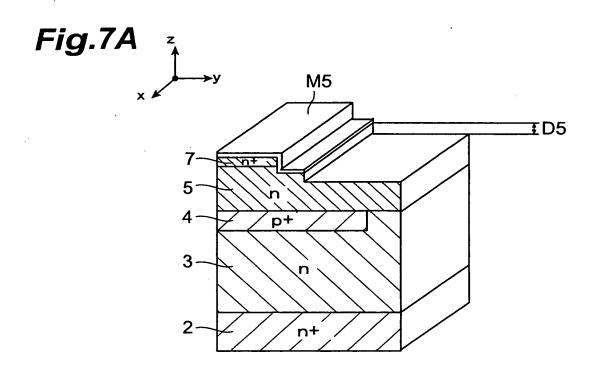
Matter No.: 14925-011US1 Page 7 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS
Page 7 of 48

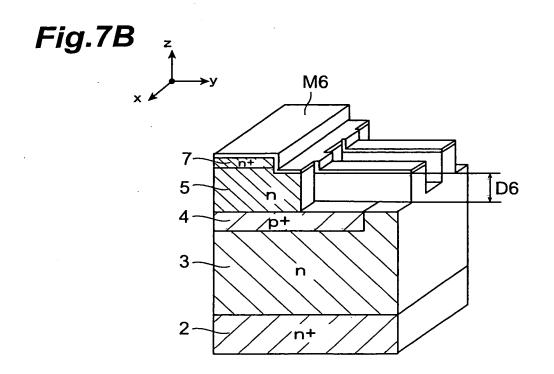
Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

Page 7 of 48

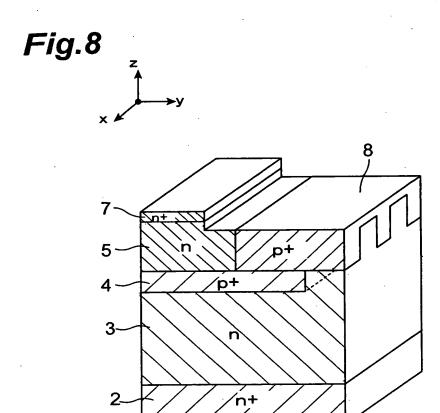
Applicant(s): Takashi Hoshino, et al.





Matter No.: 14925-011US1 Page 8 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278

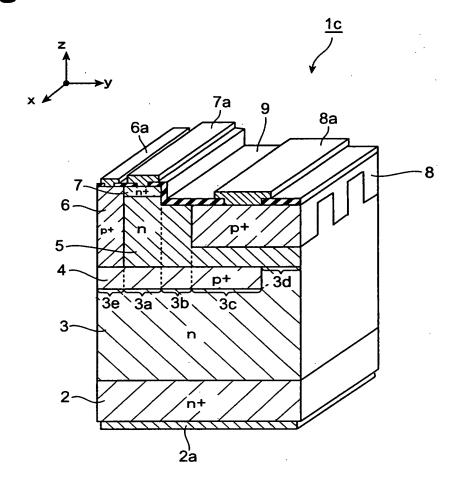


Page 9 of 48

Matter No.: 14925-011US1 Page 9 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278

Fig.9



Matter No.: 14925-011US1 Applicant(s): Takashi Hoshino, et al.

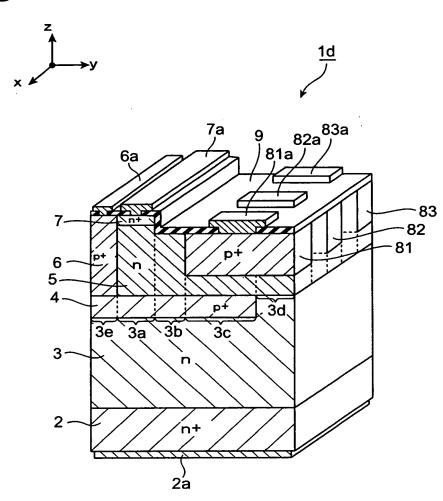
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND

METHODS OF PRODUCING THE VERTICAL JUNCTION

FIELD EFFECT TRANSISTORS

10/522278

Fig.10

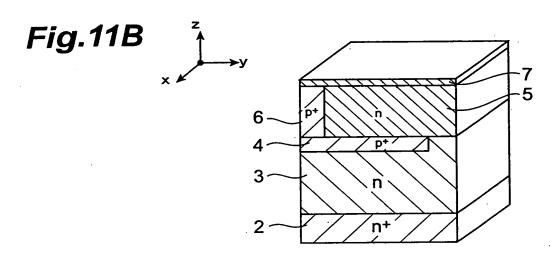


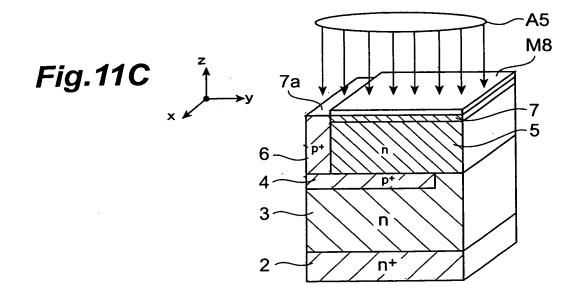
Matter No.: 14925-011US1 Page 11 of 48 Applicant(s): Takashi Hoshino, et al. VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION

10/522278

11/48

FIELD EFFECT TRANSISTORS

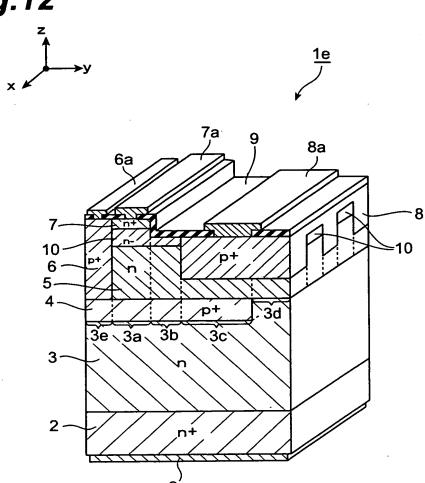




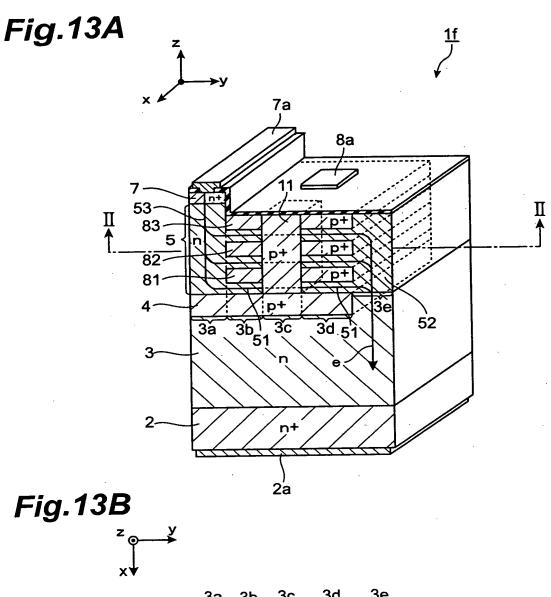
Matter No.: 14925-011US1 Page 12 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278

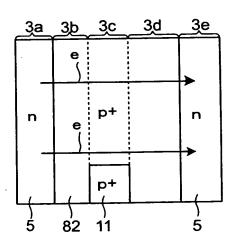
Fig.12



10/522278







Matter No.: 14925-011US1 Page 14 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

10/522278

Fig.14A

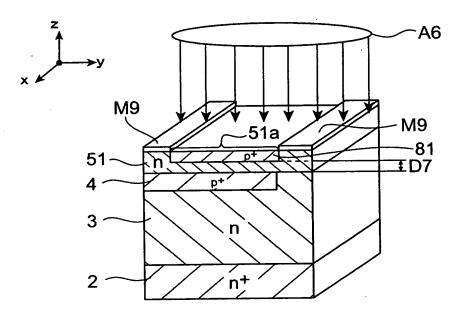
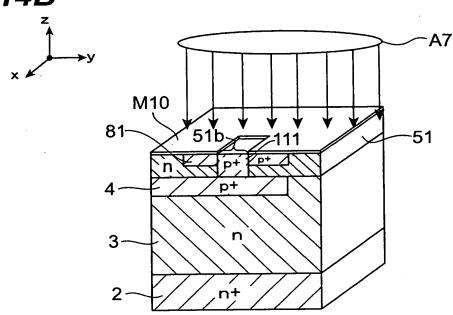
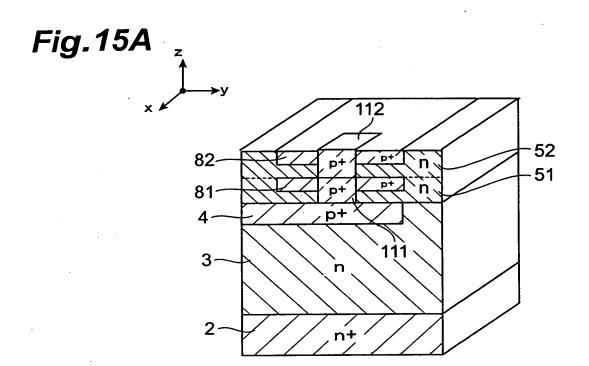
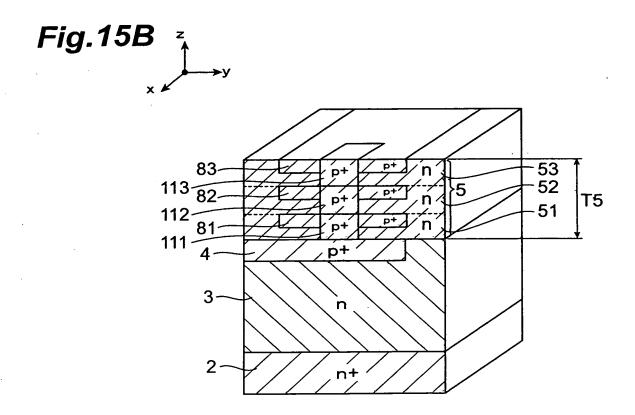


Fig.14B



Matter No.: 14925-011US1 Page 15 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT-TRANSISTORS





Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND

METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

10/522278

Fig.16A

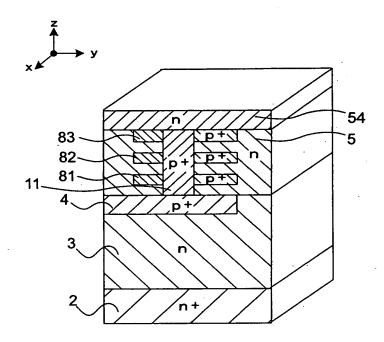
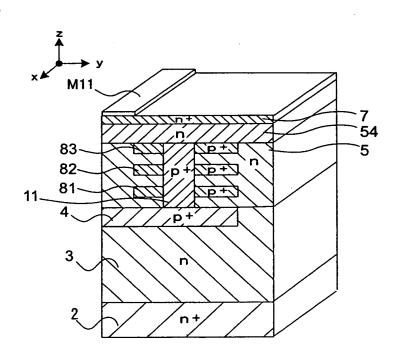


Fig.16B



10/522278

Fig.17A

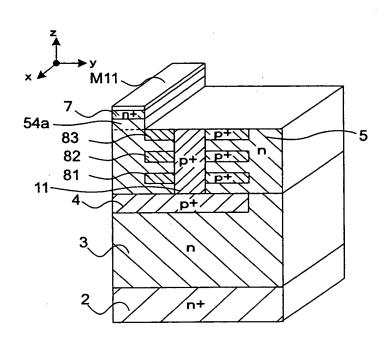
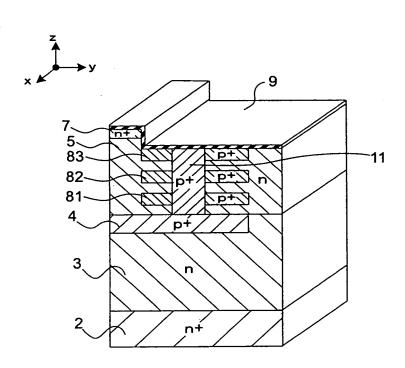
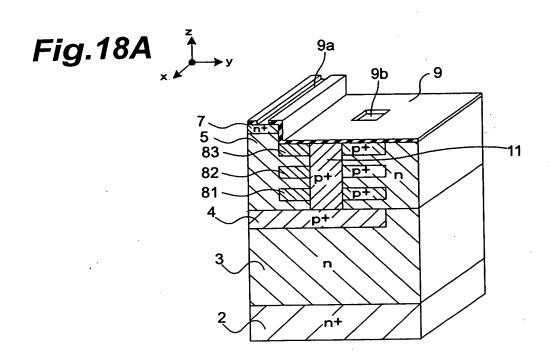


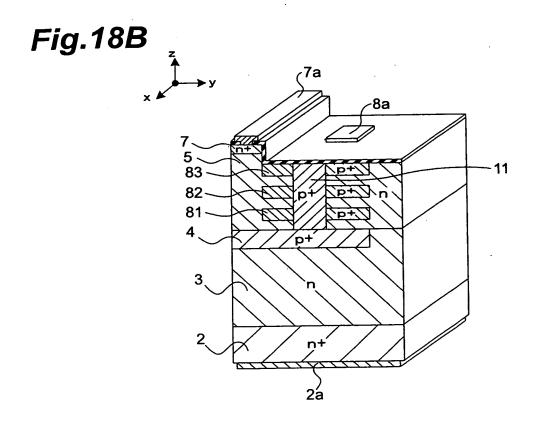
Fig.17B



FIELD EFFECT TRANSISTORS

10/522278





Matter No.: 14925-011US1

Page 19 of 48

Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND

METHODS OF PRODUCING THE VERTICAL JUNCTION

FIELD EFFECT TRANSISTORS

19/48

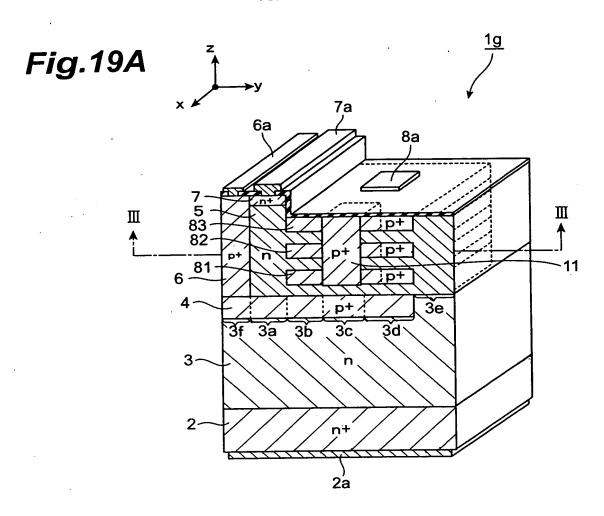
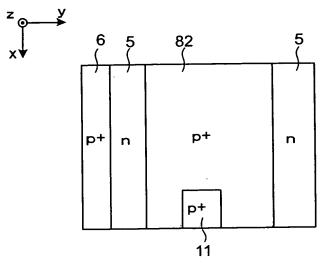


Fig.19B



Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

10/522278

Fig.20A

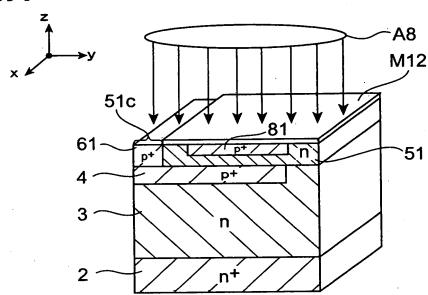
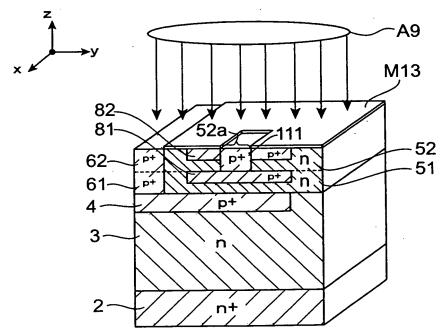
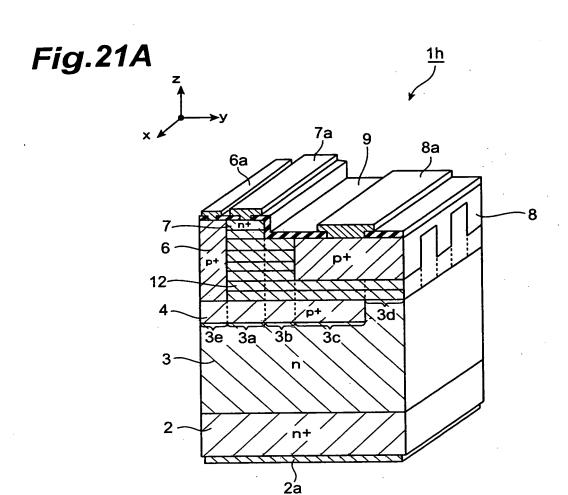


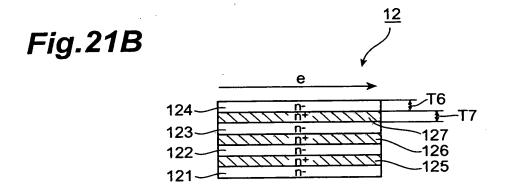
Fig.20B



Matter No.: 14925-011US1 Page 21 of 48 Applicant(s): Takashi Hoshino, et al. VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND

METHODS OF PRODUCING THE VERTICAL JUNCTION 10/52227 8





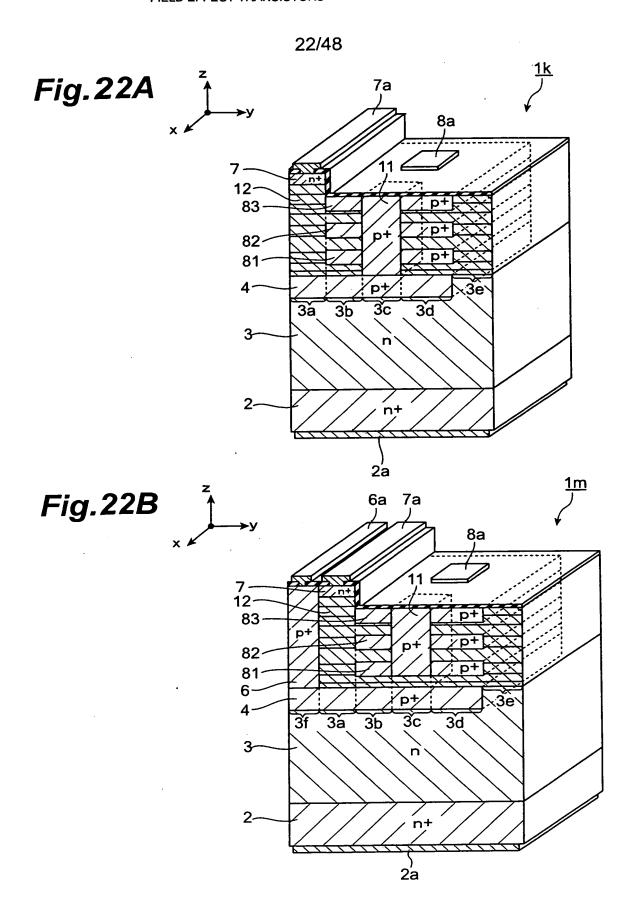
Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND

METHODS OF PRODUCING THE VERTICAL JUNCTION

10/522278

FIELD EFFECT TRANSISTORS

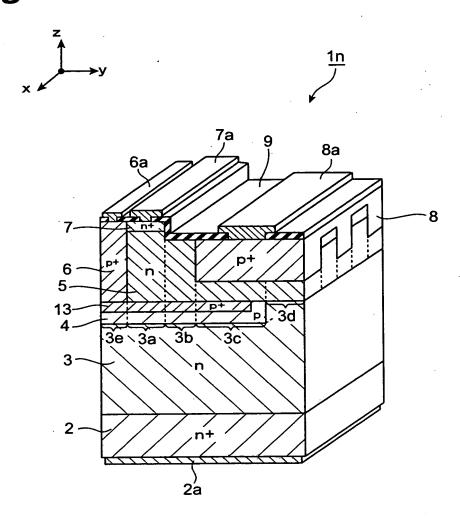


Matter No.: 14925-011US1 Page 23 of 48 Applicant(s): Takashi Hoshino, et al.

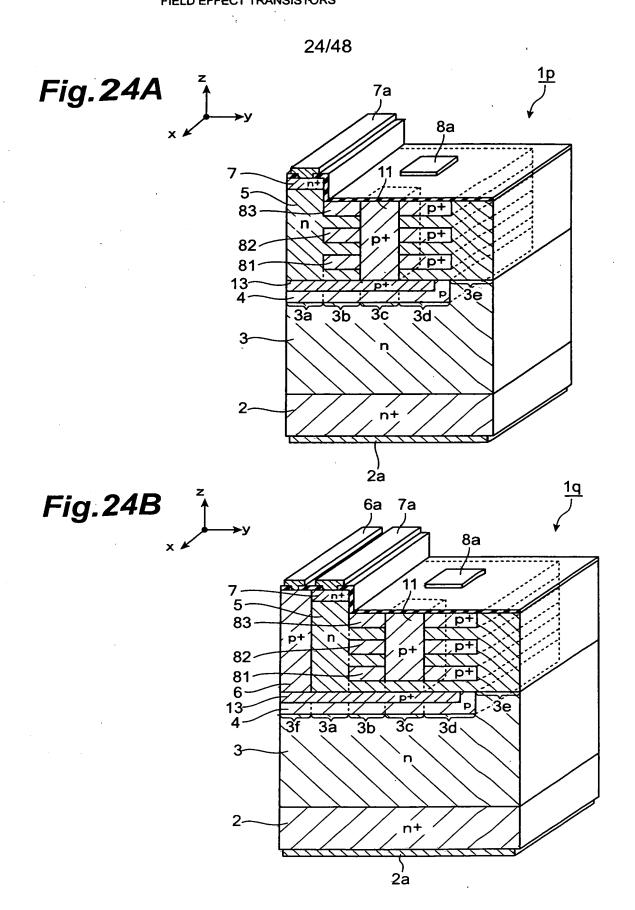
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

10/522278

Fig.23



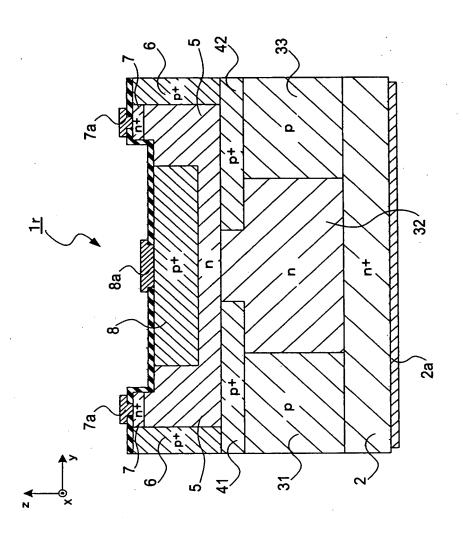
Matter No.: 14925-011US1 Applicant(s): Takashi Hoshino, et al. VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS



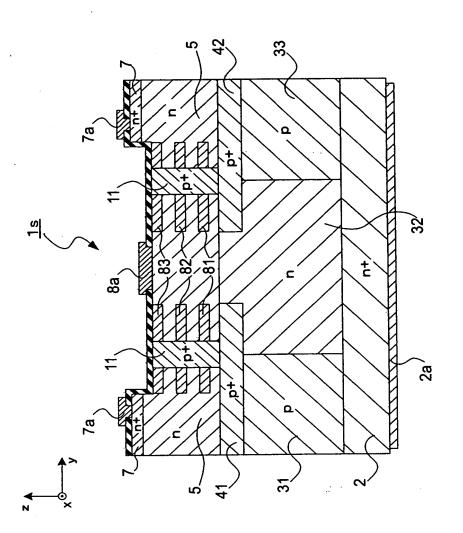
Page 25 of 48

Matter No.: 14925-011US1 Page 25 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278



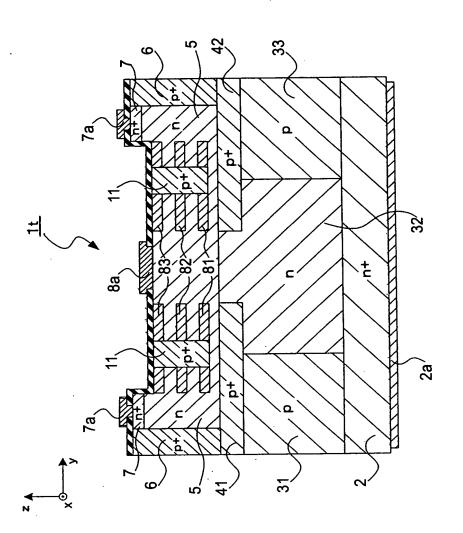
10/522278



Page 27 of 48

Matter No.: 14925-011US1 Page 27 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278



Matter No.: 14925-011US1

Page 28 of 48

Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION

FIELD EFFECT TRANSISTORS

28/48

Fig.28A

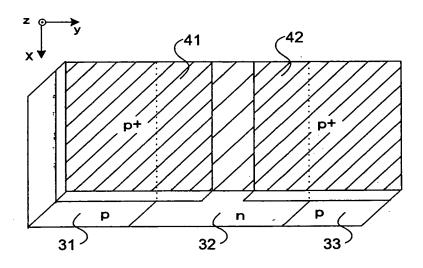


Fig.28B

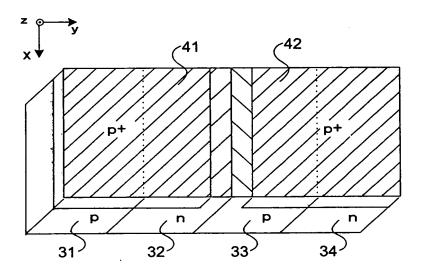
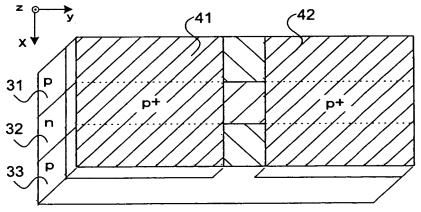
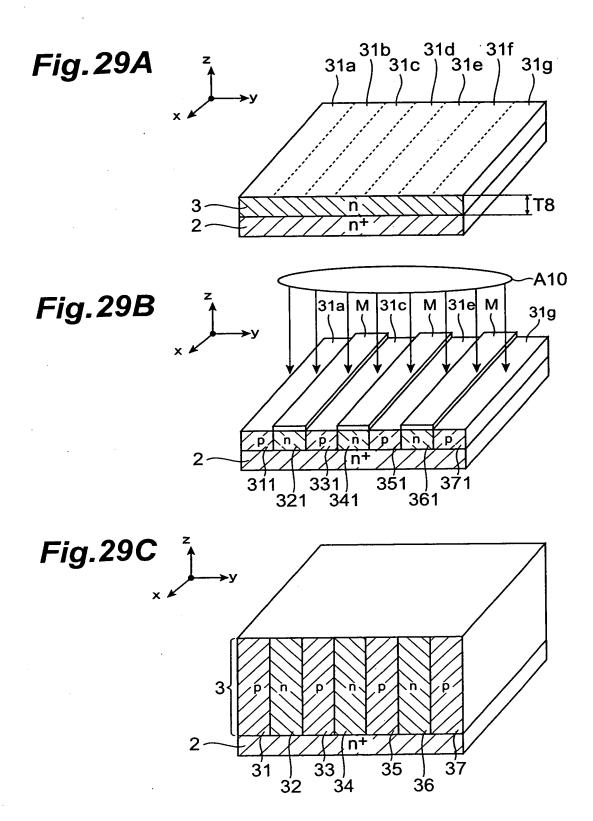


Fig.28C *



Matter No.: 14925-011US1 Page 29 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

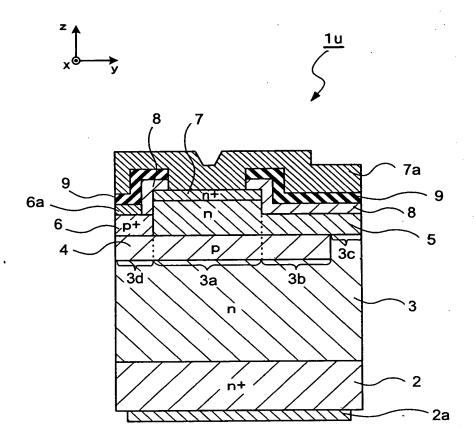
10/522278



Matter No.: 14925-011US1 Page 30 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278

Fig.30



VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

10/522278

Fig.31A



Fig.31B

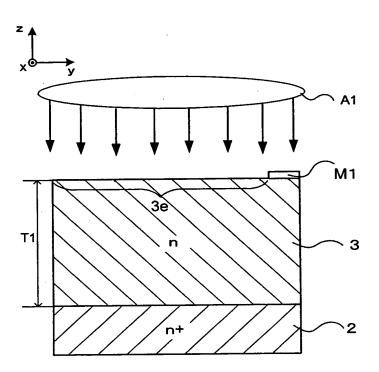
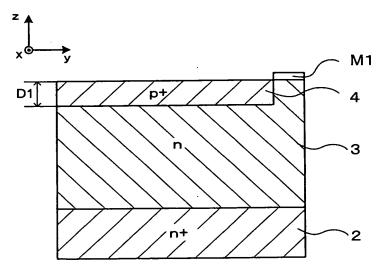


Fig.31C



Matter No.: 14925-011US1

Page 32 of 48

Applicant(s): Takashi Hoshino, et al. VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

10/522278

Fig.32A

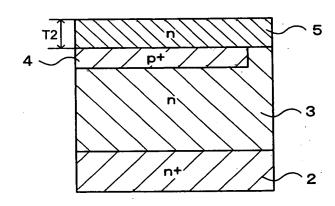


Fig.32B

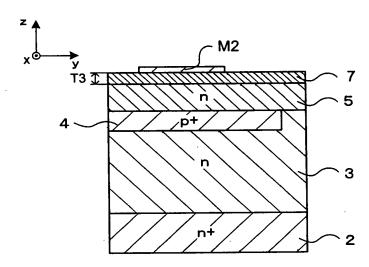
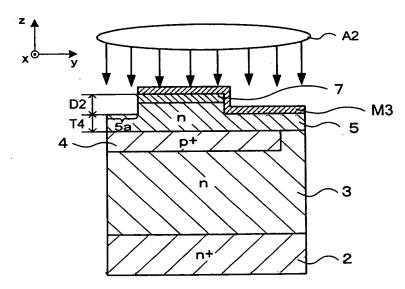


Fig.32C



Page 33 of 48

Matter No.: 14925-011US1

Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND

METHODS OF PRODUCING THE VERTICAL JUNCTION

FIELD EFFECT TRANSISTORS

10/522278

Fig.33A

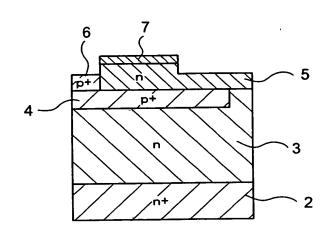


Fig.33B

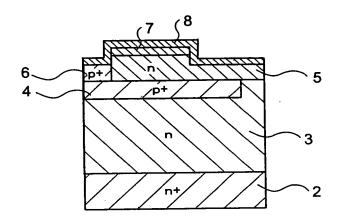
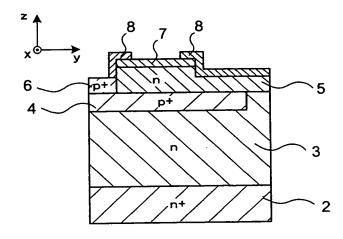


Fig.33C



10/522278

Fig.34A

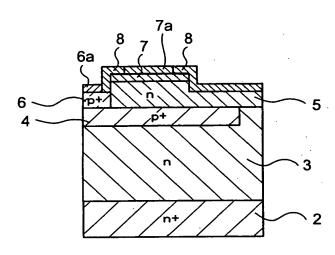


Fig.34B

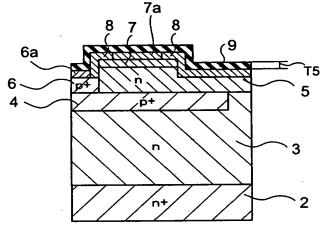
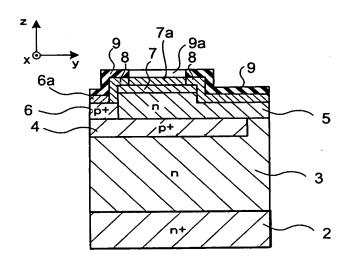


Fig.34C



Matter No.: 14925-011US1 Page 35 of 48

Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND

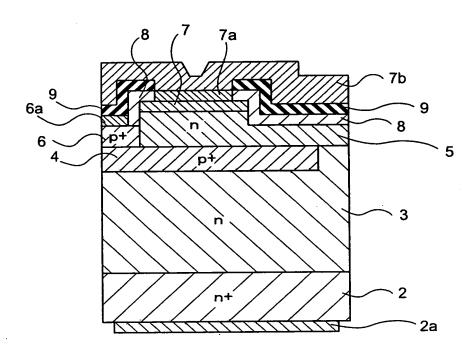
METHODS OF PRODUCING THE VERTICAL JUNCTION

FIELD EFFECT TRANSISTORS

Page 35 of 48

10/522278

Fig.35

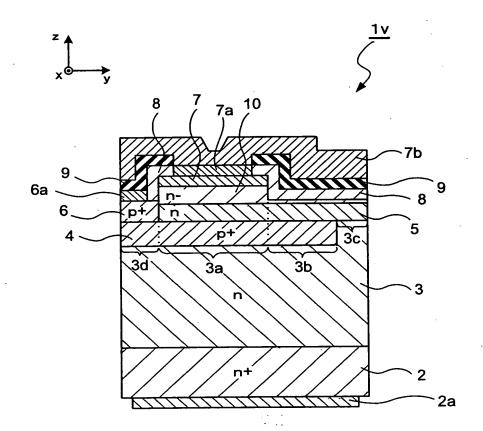


Matter No.: 14925-011US1 Page 36 of 48 Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278

Fig.36



Matter No.: 14925-011US1 Page 37 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/5-2227 8

Fig.37A

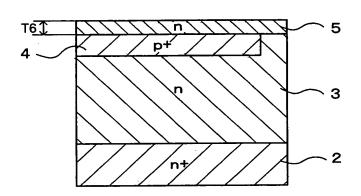


Fig.37B

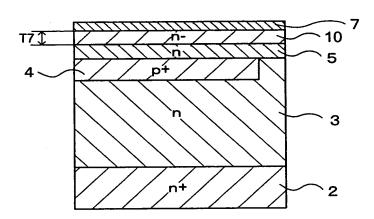
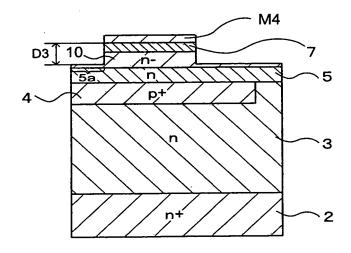


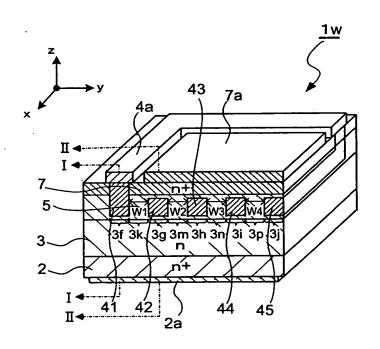
Fig.37C



Matter No.: 14925-011US1 Page 38 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522275

Fig.38

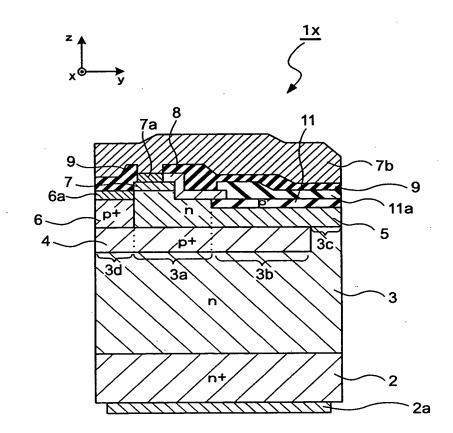


Page 39 of 48

Matter No.: 14925-011US1 Page 39 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522276

Fig.39



10/522278

Fig.40A

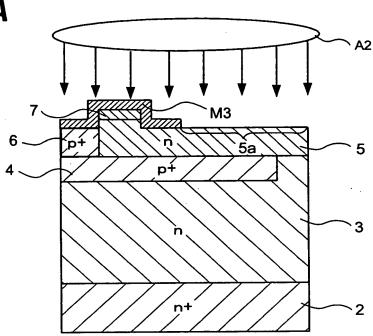
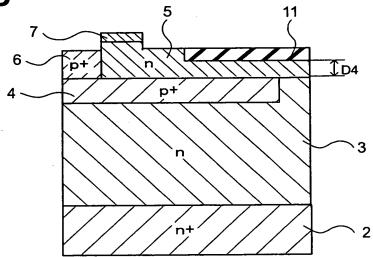


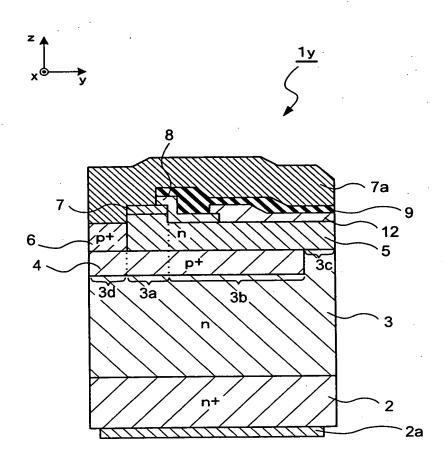
Fig.40B



Matter No.: 14925-011US1 Page 41 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

10/522278

Fig.41



Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND

METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

10/522278

Fig.42A

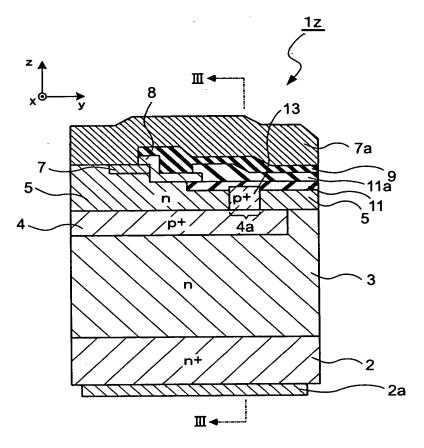
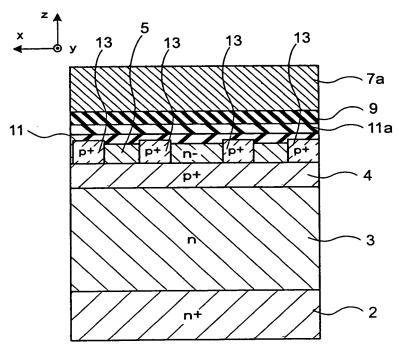
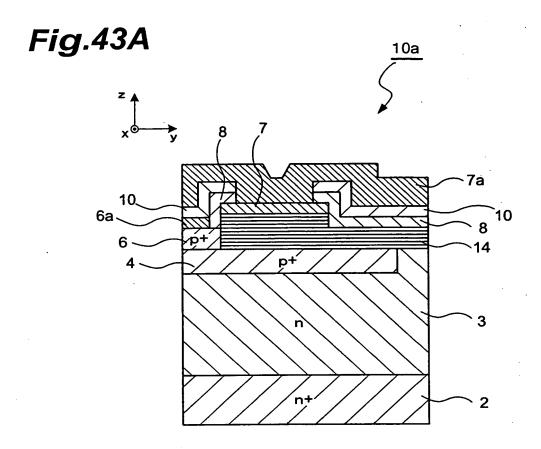
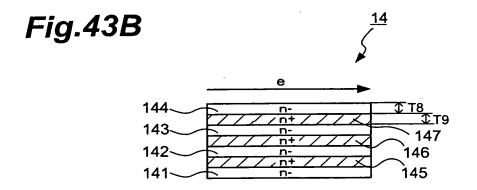


Fig.42B



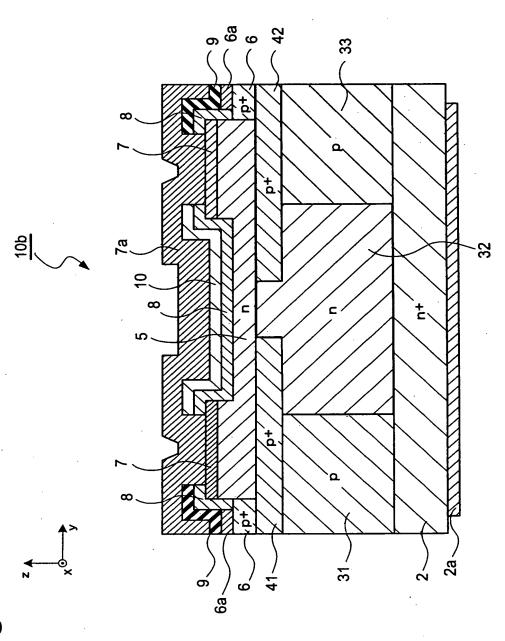




Page 44 of 48

Matter No.: 14925-011US1 Page 44 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

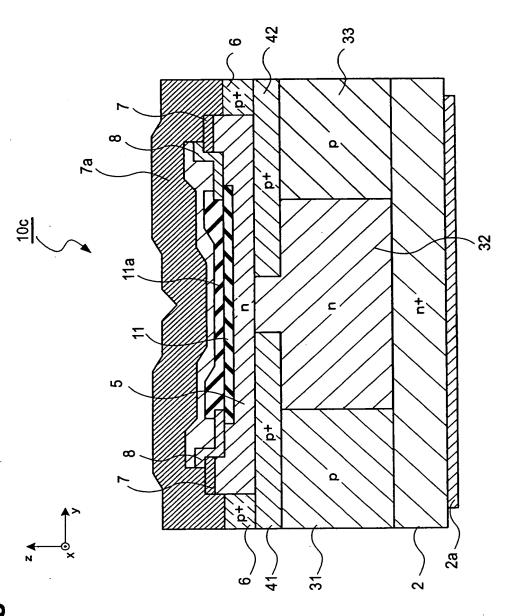
10/522278



Page 45 of 48

Matter No.: 14925-011US1 Page 45 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

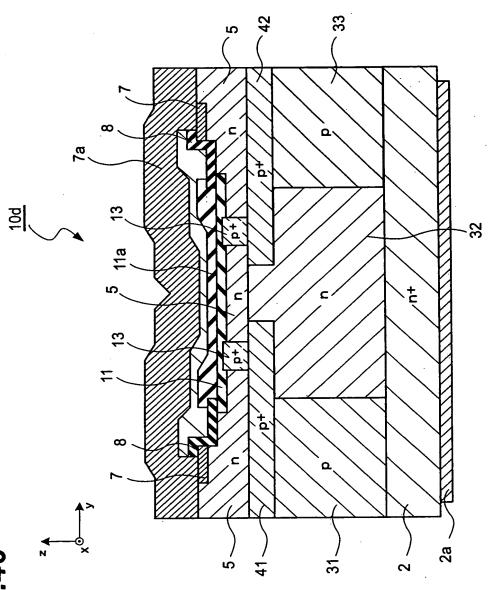
45/48



Page 46 of 48

Matter No.: 14925-011US1 Page 46 of 48
Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION
FIELD EFFECT TRANSISTORS

46/48



Matter No.: 14925-011US1 Page 47 of 48

Applicant(s): Takashi Hoshino, et al.

VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND METHODS OF PRODUCING THE VERTICAL JUNCTION FIELD EFFECT TRANSISTORS

47/48

Fig.47A

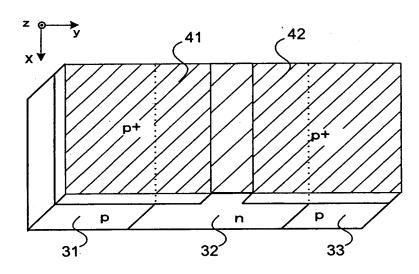


Fig.47B

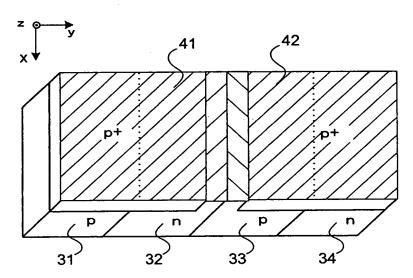
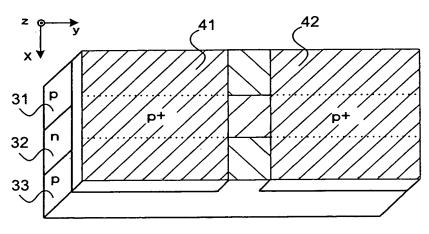


Fig.47C



Applicant(s): Takashi Hoshino, et al.
VERTICAL JUNCTION FIELD EFFECT TRANSISTORS, AND
METHODS OF PRODUCING THE VERTICAL JUNCTION

FIELD EFFECT TRANSISTORS

10/522278

